

RAW MATERIAL FOR CHEMICAL VAPOR DEPOSITION AND METHOD FOR PRODUCING THIN FILM USING THE SAME

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Abstract

PROBLEM TO BE SOLVED: To obtain a raw material including group 4 elements such as titanium, zirconium and hafnium suitable for producing a thin film by a CVD method, and also provide a method for producing the thin film using the material.

SOLUTION: The raw material for chemical vapor deposition includes a metallic compound expressed by general formula (I) (wherein, M is titanium, zirconium or hafnium, R1, R2 and R5 are each independently an alkyl group which may include one or two oxygen atoms in a 1-8C chain; R3 and R4 are each independently H or a 1-4C alkyl group; A is a 1-4C alkylene group; and (n) is 0, 1 or 3 when M is titanium and 0, 1, 2 or 3 when M is zirconium or hafnium).

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